

<b>SPEC SHEET (FOR REFERENCE)</b>	SHEET No.	Rev.	Page.
	<b>G05066A</b>		1 of 1

TYPE : 6PT2206N4T\*\*

CHIP SIZE	0.4 * 0.4 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	95,200 pcs

Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	60	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	0.3	A

\* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	VGSS 1	20			V	IG= 10uA
2	VGSS 2	-20			V	IG= -10uA
3	IGSS 1			1	uA	VGS= 10V
4	IGSS 2			-1	uA	VGS= -10V
5	IGSS 3			10	uA	VGS= 20V
6	IGSS 4			-10	uA	VGS= -20V
7	IDSS 1			50	nA	VDS= 60V
8	BVDSS	60			V	ID= 10uA
9	Vth	0.5	1	1.5	V	ID= 250uA
10	RDS(on) 1		1	1.4	Ω	ID= 220mA VGS= 10V
11	RDS(on) 2		1.1	2.0	Ω	ID= 220mA VGS= 4.5V
12	VSD L	0.5			V	IS= 220mA VGS= 0V
13	VSD H			1.4	V	IS= 220mA VGS= 0V
14	Yfs	220			mS	VDS= 10V ID= 220mA

※ Built-in ZD between Gate and Source. ESD Protected.

TENTATIVE

NOTE: